

WAFER PROFILER CVP21

ECV Measurement of **Doping Profiles** for **Solar Cell, IC, Photonics, and more**

Patents: DE-10256821, US-7026255 (further pending)



CVP21 including option FP: Footprint
60*80cm for minimum required clean room
space

太阳能电池P-N 结深 Solar Cell Doping Profile

COMPLETE Material Range:

Group IV: Si, Ge, SiC
Standard III-V: GaAs, InP, ...
Ternary: AlGaAs, GaInP, ...
Quaternary: AlGaInP, ...
Nitrides: GaN, AlGa N, AlInN, ...
II-VI: ZnO, CdTe, CdHgTe, ...

COMPLETE Sample Range:

Stacked layers no problem
No restrictions concerning substrate
Sample size: 4*2 mm² ... 8" Wafer

COMPLETE Resolution Range:

< 10¹² cm⁻³ ... > 10²¹ cm⁻³ (*)
1 nm ... 100 μm (*)
(*) may depend on material type/ sample quality.
Please ask for sample measurements.

COMPLETE System:

HiRel -Calibration-free -Easy-to-Use
Wafer-Stepping -Camera-Control
Recipes -Auto-Load/Unload/Reload
Manual/SemiAuto/FullAuto

中国指定服务经销商

塞伦
Saratoga

赛伦科技总部

Saratoga Technology International
20225 Seagull Way
Saratoga, California 95070, USA
Tel: +1 (408) 420-3561
Email: info@saratogatek.com
Web: www.saratogatek.com

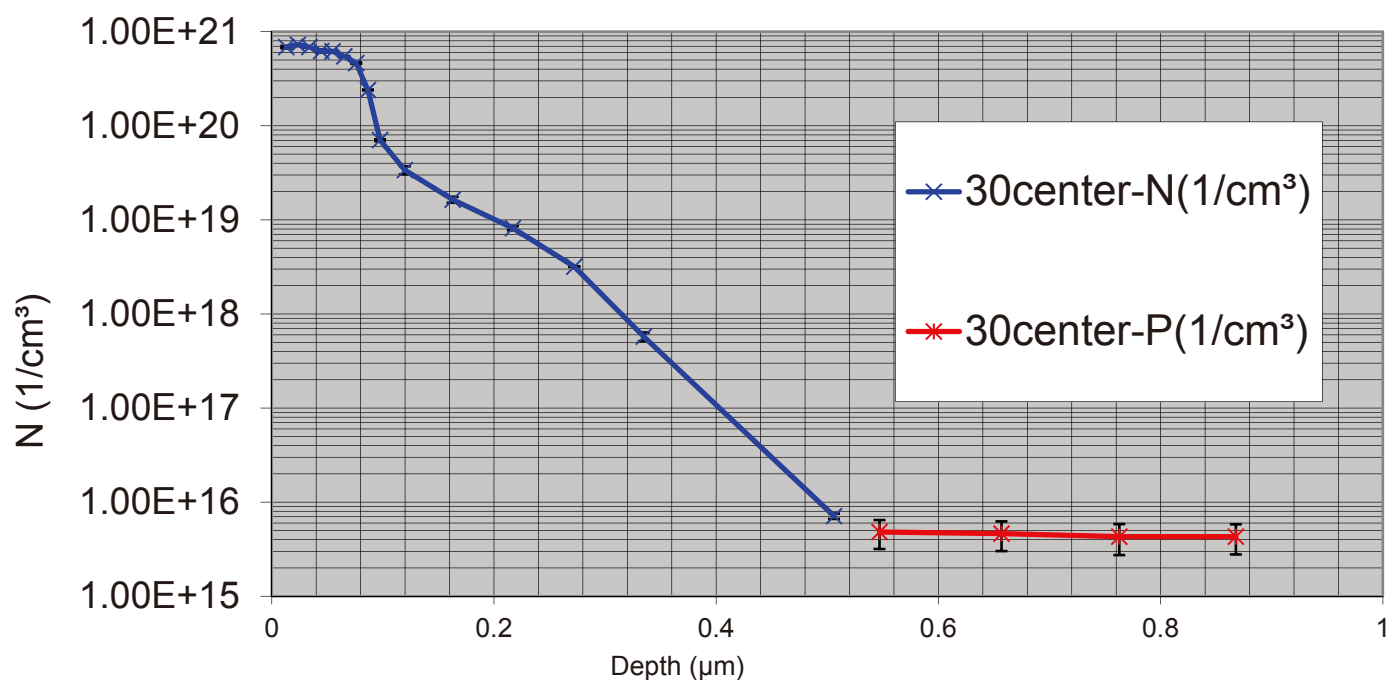
赛伦科技上海

上海市黄浦区陆家浜路1378号
万事利大厦1102室
邮编 200011
电话: +86 (021) 6136 3596
手机: 13817915874
中文网址: www.saratogatek.com.cn

赛伦科技北京

北京海淀区中关村东路89号
恒兴大厦三层311室
邮编100190
电话: +86 (010) 6256 1331
手机: 13601118327

Typical results:



ECV Profiling -Solution Advantages:

	Hall	SIMS Secondary Massion Spectroscopy	SRP Spreading Resistance Profiling	ECV Electrochemical CV-Profiling
Monitor the doping concentration	✓	✓	✓	✓
Monitor the electrical activation of dopants, including doping type	✗	✗	✗	✓
n/p Monitor the crystalline quality of the sample	✗	✗	✗	✓
Easy sample preparation	✗	✗	✗	✓
The substrate may be conductive	✗	✓	✓	✓
The thickness of the epi layer may be unknown	✗	✓	✓	✓
The depth profile may be measured with a resolution down to 1nm	✗	✓	✗	✓
Several layers may be measured	✗	✓	✓	✓
A wide range of materials may be analyzed	✓	✓	✗	✓
Concentrations below 10 ¹⁴ cm ⁻³ may be measured	✓	✗	✗	✓
Easy equipment preparation (no tedious calibration required)	✓	✗	✗	✓
Wafer topography may be measured on a complete wafer	✗	✗	✗	✓
PEC etching (Photo-Electrochemical etching) may be evaluated	✗	✗	✗	✓
The surface may be etched/passivated at start of the measurement	✗	✓	✗	✓

Manufactured by WEP

Furtwangen, Germany

+49-7723-9197-0

www.wepcontrol.com